DATA SHEET



SILICON TRANSISTOR ARRAY $\mu PA1478$

NPN SILICON POWER TRANSISTOR ARRAY LOW SPEED SWITCHING USE (DARLINGTON TRANSISTOR) INDUSTRIAL USE

DESCRIPTION

The μ PA1478 is NPN silicon epitaxial Darlington Power Transistor Array that built in Surge Absorber and 4 circuits designed for driving solenoid, relay, lamp and so on.

FEATURES

- Surge Absorber (Zener Diode) built in.
- Easy mount by 0.1 inch of terminal interval.
- High hre for Darlington Transistor.

ORDERING INFORMATION

Part Number	Package	Quality Grade
μΡΑ1478Η	10 Pin SIP	Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

Vсво	31 ±4	V
Vceo	31 ±4	V
Vebo	7	V
Eceo (sus)	40	mJ/unit
C(DC)	±2	A/unit
C(pulse)*	± 4	A/unit
PT1**	3.5	W
PT2***	28	W
ΤJ	150	°C
Tstg -5	5 to +15	50 °C
	VCEO VEBO ECEO (SUS) IC(DC) IC(pulse)* PT1** PT2*** TJ	VCEO 31 ±4 VEBO 7 ECEO (SUS) 40 IC(DC) ±2 IC(pulse)* ±4 PT1** 3.5 PT2*** 28 TJ 150

- * PW \leq 300 μ s, Duty Cycle \leq 10 %
- ** 4 Circuits, Ta = 25 °C
- *** 4 Circuits, $T_c = 25$ °C



The information in this document is subject to change without notice.

ELECTRICAL CHARACTERISTICS (TA = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
Collector Leakage Current	Ісво			10	μA	$V_{CB} = 20 V, I_E = 0$	
Emitter Leakage Current	Ево			1	mA	$V_{EB} = 5 V$, Ic = 0	
Collector to Emitter Sustaining Voltage	Vceo(sus)	27	31	35	V	lc = 1 A, L = 3 mH	
DC Current Gain	hfe1 *	1000			—	Vce = 2 V, Ic = 0.5 A	
DC Current Gain	hfe2 *	2000		30000	_	Vce = 2 V, Ic = 1 A	
Collector Saturation Voltage	VCE(sat) *			1.5	V	Ic = 1 A, IB = 1 mA	
Base Saturation Voltage	VBE(sat) *			2	V	Ic = 1 A, IB = 1 mA	
Turn On Time	ton		0.5		μs	Ic = 1 A	
Storage Time	tstg		3		μs	I _{B1} = −I _{B2} = 1 mA Vcc ≑ 20 V, RL ≑ 20 Ω See test circuit	
Fall Time	tr		1		μs		

* PW \leq 350 μ s, Duty Cycle \leq 2 % / pulsed

SWITCHING TIME TEST CIRCUIT



The application circuits and their parameters are for references only and are not intended for use in actual design-in's.















VcE (sat) - Collector Saturation Voltage - V



REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134

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Application examples recommended by NEC Corporation

Standard: Computer, Office equipment, Communication equipment, Test and Measurement equipment, Machine tools, Industrial robots, Audio and Visual equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.

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